

UNISONIC TECHNOLOGIES CO., LTD

MGBR10U300 DIODE

MOS GATED BARRIER RECTIFIER

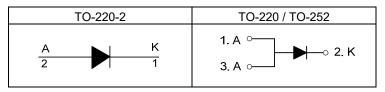
DESCRIPTION

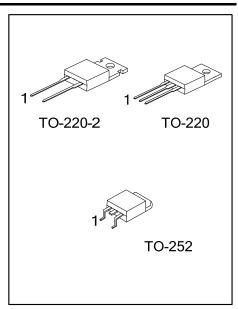
The UTC **MGBR10U300** is a surface mount mos gatedbarrier rectifier,it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

■ FEATURES

- * Ultra low forward voltage drop
- * High switching speed

■ SYMBOL

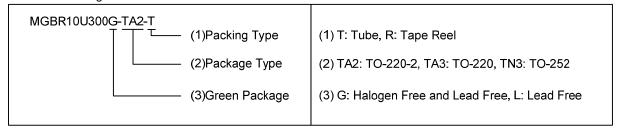




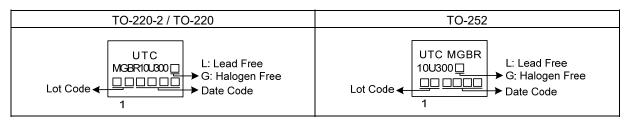
ORDERING INFORMATION

Ordering Number		Doolsogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR10U300L-TA2-T	MGBR10U300G-TA3-T	TO-220-2	K	Α	NC	Tube	
MGBR10U300L-TA3-T	MGBR10U300G-TA3-T	TO-220	Α	K	Α	Tube	
MGBR10U300L-TN3-R	MGBR10U300G-TN3-R	TO-252	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT	
DC Blocking Voltage		V_{RM}	300	V	
Working Peak Reverse Voltage		V_{RWM}	300	V	
Peak Repetitive Reverse Voltage		V_{RRM}	300	V	
Average Rectified Output Current	T _C =140°C	Io	10	Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	160	А	
Power Dissipation (T _C =25°C)	TO-220		00.5	10/	
	TO-220-2	P_{D}	62.5	W	
	TO-252		20	W	
Operating Junction Temperature		T_J	-65 ~ +150	°C	
Storage Temperature		T _{STG}	-65 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (Note 3)

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220 TO-220-2	θ_{JA}	62.5	°C/W
	TO-252		110	i
Junction to Case	TO-220 TO-220-2	Өлс	2	°C/W
	TO-252		6	

■ ELECTRICAL CHARACTERISTICS (T_A=25°C,unless otherwise specified.)

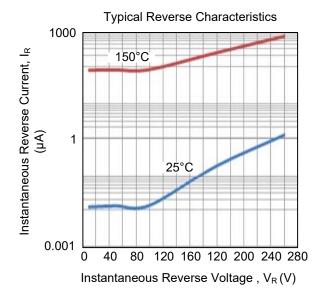
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA	300			V
Forward Voltage Drop	VEM	I _F =10A, T _J =25°C			0.85	V
		I _F =10A, T _J =125°C			0.75	V
Leakage Current (Note 1)	DM	V _R =300V, T _J =25°C			100	μΑ
		V _R =300V, T _J =125°C			10	mA

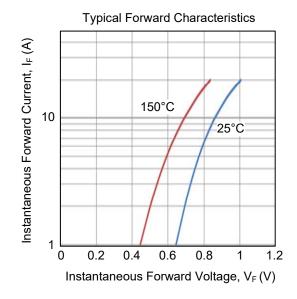
Notes: 1. Short duration pulse test used to minimize self-heating effect.

- 2. Thermal resistance junction to case mounted on heatsink.
- 3. Mounted on an FR4 PCB, single-sided copper, with 100 cm² copper pad area.

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■ TYPICAL CHARACTERISTICS





UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.